Dielectric properties of thermal and plasma-assisted atomic layer deposition Al2O3 thin films

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Dielectric Properties of Thermal and Plasma-Assisted Atomic Layer Deposited Al2O3 Thin Films

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A comparative electrical characterization study of aluminum oxide (Al2O3) deposited by thermal and plasma-assisted atomic layer depositions (ALDs) in a single reactor is presented. Capacitance and leakage current measurements show that the Al2O3 deposited by the plasma-assisted ALD shows excellent dielectric properties, such as better interfaces with silicon, lower oxide trap charges, higher tunnel barrier with aluminum electrode, and better dielectric permittivity (k ≈ 8.8), than the thermal ALD Al2O3. Remarkably, the plasma-assisted ALD Al2O3 films exhibit more negative fixed oxide charge density than the thermal ALD Al2O3 layers. In addition, it is shown that plasma-assisted ALD Al2O3 exhibits negligible trap-assisted (Poole–Frenkel) conduction unlike the thermal ALD Al2O3 films, resulting in higher breakdown electric fields than the thermal ALD prepared films.

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Among various metal oxides with medium dielectric permittivity, Al2O3 has been proposed as a promising and reliable candidate as an initial replacement for the conventional silicon oxide (SiO2) as a gate oxide material in metal-oxide-semiconductor transistors because of its higher dielectric permittivity of ∼ 8–9, low leakage current level, and high breakdown electric fields due to its large bandgap (8.8 eV).1,2 Al2O3 is known for its large band-offset with silicon, which is crucial for achieving low leakage currents through the devices.3 Moreover, Al2O3 has an excellent thermal and chemical stability, for instance, it remains amorphous until temperatures above 800°C.4 Upon using atomic layer deposition (ALD), reactive chemistries can be used which ensure very good chemisorption and growth behavior on various substrates at low deposition temperatures.5 It has been reported that Al2O3 can be deposited on silicon with very small interfacial oxide layer thickness compared to other high-k oxides,6 which makes it useful as an oxidation-barrier for the ALD processing of other high-k layers as well.7 More than as a gate oxide, Al2O3 is an important material for numerous application domains, for instance, to enhance the quantum efficiency of silicon in metal-insulator–semiconductor devices,8 to encapsulate materials and devices that are sensitive to environments such as humidity, to enhance the Q-factor of silicon cantilevers,9,10 or to enable functionalization on hydrophobic graphene and carbon nanotube surfaces for the applications in nanoelectronics.11,12 and to passivate surfaces of silicon solar cells.13 Remarkable about ALD processed Al2O3 is that the oxide can contain intrinsic negative fixed oxide charges14 that are beneficial for the applications in charge-trap flash memory devices15 and, in particular, high-efficiency silicon solar cells.16,17 With the added value of ALD achieving good conformity in the high aspect-ratio features, high capacitance density metal-insulator-metal (MIM) capacitors have been realized for the integration of passive elements.18,19

In this paper, we compare the dielectric properties of Al2O3 deposited with the thermal and plasma-assisted ALD techniques in a single reactor chamber by fabricating metal–insulator–silicon (MIS) devices. This allows us to compare between the thermal and plasma-assisted Al2O3 films independent of the possible variations in the deposition conditions of different reactors. The major differences in the processing of the films with these techniques is that in the thermal ALD, H2O is employed as the oxidizing agent, while in plasma-assisted ALD, a remote O2 plasma is used. In such a remote plasma, O2 is decomposed into oxygen radicals, which are known to be very efficient in oxidizing the aluminum atoms and the organic ligands of the chemisorbed precursor molecules.20 Here we report that this results in unique electrical properties of the plasma-assisted ALD Al2O3 over the thermal ALD Al2O3, such as enhanced tunnel barrier heights and correspondingly low leakage currents and very low trap densities, as revealed in capacitance–voltage (C–V) and current–voltage (I–V) measurements. It is also remarkable that the plasma-assisted ALD Al2O3 films exhibit a higher negative fixed oxide charge density than the thermal ALD Al2O3 layers.

Experimental

Al2O3 thin films of thicknesses ranging from 5 to 80 nm were deposited on HF-last (hydrogen fluoride)-passivated 150 mm silicon wafers (with resitivity 3–10 Ω cm) in a FlexAL ALD reactor from Oxford Instruments (Oxfordshire, UK) in the remote plasma and thermal mode. The precursor used for the Al2O3 deposition was trimethylaluminum [TMA, Al(CH3)3], Akzo-Nobel (Amersfoort, Netherlands), selective semiconductor grade) which was vapor-drawn at room temperature. Using fast switching ALD valves, a saturated precursor dose was obtained by a 20 ms vapor injection. For the plasma process, the oxidation step took place using a 400 W O2 plasma at 15 mTorr ignited for a duration of typically 2 s. The O2 also served as a purge gas because there was no indication that the O2 does react with Al(CH3)3 under the specific operation conditions used in the current work. The O2 flow was kept constant at 60 sccm during the entire cycle. A cycle time of 4 s was obtained by employing a TMA purge of 1.5 s and a postplasma-purge of 0.5 s. For the thermal ALD, H2O was vapor-drawn at room temperature and dosed in steps of at maximum 120 s. A 110 sccm Ar flow (at 15 mTorr) was used as a purge gas and a pump–purge step (7 s evacuation and 5 s purging) was found most effective in removing the residual H2O from the reactor. Typical cycle times for the thermal ALD process were 16 s. The substrate temperature was kept constant at 300°C for both the remote plasma ALD and the thermal ALD. During the ALD growth, film thickness measurements were carried out by in situ spectroscopic ellipsometry, employing a model-based analysis in which the standard Cauchy relationship is used to describe the dispersion of the refractive index of Al2O3.21 A detailed description of the material properties of the deposited films has been reported elsewhere.22 Furthermore, we want to note that the O2 plasma properties and the plasma-assisted ALD process of Al2O3 have extensively been characterized in previous work.23

Annealing of the Al2O3 films was done at 450°C in forming gas (10% H2 and 90% N2) for 30 min prior to the metal electrode depo-
of 100 nm thick films of 100 devices used for the electrical measurements had an electrode area measurem
ents were done at 10 kHz plasma-assisted ALD Al2O3, and frequency LCR meter and as-deposited thermal ALD film,
Al2O3 to interface states due to the defects such as Si dangling bonds at the an as-deposited thermal ALD film,
contains a significant number of mobile charges paratively larger in these films. The curves exhibit a hysteresis of
forward and reverse sweeps, indicating that the trap density is com-
ness. A 500 nm thick aluminum layer was sputter deposited on top
of these thin films as an electrode material through a shadow mask: to form Al/Al2O3/Si MIS capacitor test devices. Primarily two tech-
niques were used for the electrical characterization of the capacitors, namely C–V measurements using an HP (Houston, Texas) multifre-
cy LCR meter and I–V measurements with an Agilent 4155C (Lexington, USA) semiconductor parameter analyzer. Capacitance measurements were done at 10 kHz (50 mV) ac modulation. The devices used for the electrical measurements had an electrode area of 100 μm × 100 μm.

Results and Discussion

Figure 1 shows the C–V characteristics of the capacitors with 10 nm thick films of (Fig. 1a) as-deposited thermal ALD Al2O3, (Fig. 1b) annealed thermal ALD Al2O3, (Fig. 1c) as-deposited plasma-assisted ALD Al2O3, and (Fig. 1d) annealed plasma-assisted ALD Al2O3. In both the thermal ALD and plasma-assisted ALD cases, forming gas annealing (FGA) appears to have a considerable influence on the device properties. The as-deposited thermal ALD Al2O3 films exhibit poor C–V curves with shoulders that correspond to interface states due to the defects such as Si dangling bonds at the Al2O3/Si interface. These characteristic bumps are seen both in forward and reverse sweeps, indicating that the trap density is comparatively larger in these films. The curves exhibit a hysteresis of ~0.3 V and a large flatband voltage shift, indicating that the oxide contains a significant number of mobile charges (such as oxygen vacancies and ions diffused into the oxide layer from the ambient). Upon FGA, the flatband shift and hysteresis are reduced (< 0.2 V) and the capacitance at accumulation condition has been enhanced by 23%. The reverse characteristic shows a smoother behavior as well, although the stretch out is still very significant. This indicates that the traps are still present but could be partially filled in the forward sweep and captured there, resulting in a smaller hysteresis.

The as-deposited plasma-assisted ALD films show better C–V characteristics compared with the thermal ALD films. These films also exhibit interface states, but unlike the thermal ALD films, they do not show characteristic bumps due to the trap levels in depletion, indicating that the oxide–silicon interface does not trap a significant number of charges. Upon FGA, the C–V curves become much smoother and no interface states are observed anymore. Upon FGA, two competing processes can occur in terms of the thickness of the films: a slight reduction in the thickness due to further densification and a slight increase in the thickness due to passivation of the defect by the incorporation of nitrogen or hydrogen atoms. The saturation capacitance of the thermal ALD films increases by approximately 4%, which could be due to a slight densification of the film during FGA. Conversely, the as-deposited plasma-assisted ALD films are already denser than the thermal ALD films, as has been reported before. Therefore, the dominating effect should be a minor swelling of the films, resulting in a slight reduction in the saturation capacitance upon FGA, as shown in Fig. 1.

Figure 2 depicts the equivalent oxide thickness (EOT) calculated for films with different thicknesses deposited with (Fig. 2a) the thermal ALD and (Fig. 2b) the plasma-assisted ALD techniques. To estimate the EOT, the expression EOT = e0 × kSiO2/(C/A) was employed, assuming that the interfacial SiO2 layer has a dielectric constant of kSiO2 = 3.9. From the slope of these plots, the k-values of the stacks can be estimated from the expression k = kSiO2 × (d/EOT). A k-value of 6.7 was estimated for the as-deposited thermal ALD films, remaining practically the same (at 6.5) upon FGA. As evident from Fig. 2a, FGA does not have any significant influence on the dielectric properties, but it improves the interface quality with the electrodes. In contrast, the as-deposited plasma-assisted ALD films
The flatband shift can be expressed as:

\[ V_{FB} = \phi_{MS} - (Q_f + Q_d) \frac{d}{e k} - \frac{1}{e k x} \int_0^d [\rho_m(x) + \rho_d(x)] dx \]  

where \(\phi_{MS}\) is the work-function difference between the metal electrode and the silicon substrate. The second term represents the contribution to the mirror charge in the semiconductor conduction band from the sum of the fixed oxide charge \((Q_f)\) and the oxide trap charges at the interface \((Q_d)\). The third term represents the mobile charges and the oxide trap charges in the oxide, which are responsible for the hysteresis in the C-V curves (here \(\rho_m(x)\) and \(\rho_d(x)\) represent the mobile and oxide trap charge densities, respectively).

The positive flatband shift in all C-V curves of the plasma-assisted ALD samples indicates that the fixed oxide charges and the interface trap charges are negatively charged. This is in line with what has been reported by Wilk et al.\(^2\) and what Hoex et al. have demonstrated for the plasma-assisted ALD Al\(_2\)O\(_3\) films earlier.\(^14\) The thermal ALD films do not show a gradual flatband shift with the oxide thickness, which might indicate that the mobile charges and the sum of the fixed oxide charges and the oxide trap charges at the interface have opposite signs and their effect cancel out eventually. Conversely, the plasma-assisted ALD films exhibit a gradual linear increase in \(V_{FB}\). In these samples, the mobile and oxide trap charges are significantly less because the C-V curves do not show considerable hysteresis. Therefore, it can be safely assumed that the integral part of Eq. 1 is negligibly small for the plasma-assisted ALD films. Thus, from the slope of the data in Fig. 3a and b, the total of the fixed oxide and interface trap charges \(Q\) can be estimated using:

\[ Q = \frac{V_{FB} \rho_d \Delta E}{EOT} \]  

with \(e\) being the elementary charge.

For the as-deposited plasma-assisted ALD Al\(_2\)O\(_3\) devices this estimation yields a negative charge density of \(-9.5 \times 10^{12} \text{ cm}^{-2}\), which reduces to \(-5.0 \times 10^{12} \text{ cm}^{-2}\) after FGA. In comparison, this density is within the range of the negative fixed charge densities of \(5 \times 10^{12} \text{ cm}^{-2}\) to \(1 \times 10^{13} \text{ cm}^{-2}\) observed earlier for the plasma-assisted ALD Al\(_2\)O\(_3\) films deposited at 200°C and annealed at 425°C in N\(_2\) atmosphere\(^14\) and for the plasma-assisted Al\(_2\)O\(_3\)/TiN stacks deposited at 400°C.\(^19\) The negative fixed charge density is two times smaller than the fixed oxide charge density of \(1.15 \times 10^{13} \text{ cm}^{-2}\) reported for the thermal Al\(_2\)O\(_3\) after postdeposition annealing at a much higher temperatures such as 700°C.\(^20\)

Figure 4a shows the comparison of the \((J-V)\) characteristics of the as-deposited and annealed samples, represented as the current density versus electric field \((J-E)\) plots of 10 nm Al\(_2\)O\(_3\) deposited using thermal ALD. The electric field was defined as the applied voltage across the electrodes divided by the total film thickness measured using in situ spectroscopic ellipsometry and X-ray reflectometry. It is seen that by forming gas annealing, the electrical properties such as the leakage current and the tunneling behavior of the films have improved appreciably.

Figure 4b shows the comparison of the \((J-E)\) characteristics of the as-deposited Al\(_2\)O\(_3\) film with annealed plasma-assisted ALD Al\(_2\)O\(_3\) film. Apparently, there is not much change in the leakage behavior of the plasma-assisted ALD film upon annealing, except a minor reduction of the leakage current before Fowler–Nordheim (F−N) tunneling sets in close to an electric field of 6 MV/cm. The onset for Fowler–Nordheim charge conduction increases upon annealing for the thermal ALD films (3.5 MV/cm) but does not reach the onset for F−N for the plasma-assisted ALD films (6 MV/cm). From the \((J-V)\) measurements of ten devices distributed on different locations of the wafer, the average breakdown field of the thermal ALD Al\(_2\)O\(_3\) is \(-5 \pm 0.8 \text{ MV/cm}\), whereas that of the plasma-assisted ALD film is \(-9 \pm 0.5 \text{ MV/cm}\) upon electron injection from the Al top electrode.

Figure 5 shows the Arrhenius behavior of the current density \(J\) of 10 nm thick Al\(_2\)O\(_3\) films deposited with thermal and plasma-assisted
Figure 4. (Color online) Current density J as a function of an applied electric field E as deduced from the I–V measurements on the as-deposited and annealed Al2O3 films deposited with (a) thermal ALD and (b) plasma-assisted ALD. Negative bias is applied to the Al top electrode.

Figure 5. (Color online) Arrhenius behavior of the current density of the Al2O3 films deposited using thermal ALD, (a) as-deposited and (b) annealed films; and plasma-assisted ALD, (c) as-deposited and (d) annealed films. Each data point is the average of 1000 current points measured over three different devices. The error-bars of the data are smaller than the symbols.

The leakage current at high electrical fields through a dielectric material as a result of F–N tunneling is given by:

$$J_{F-N} = CE \exp \left( -\frac{q \epsilon_t}{kT} \right)$$

where $$\epsilon_t$$ is the trap ionization energy, as derived from the Arrhenius behavior, and $$\epsilon_t$$ is the dynamic dielectric constant of the film.

Because of the Al2O3/Si conduction band-offset is 2.8 eV, the effect of Schottky emission of electrons can be ignored. From the Arrhenius behavior, we can conclude that the leakage current through the thermal ALD films is more sensitive to temperature than through the plasma-assisted ALD films and indicates that the electric conduction mechanism could be significantly influenced by the trap levels distributed below the conduction band of the thermally deposited oxide films. Therefore, the role of Poole–Frenkel (P–F) conduction cannot be neglected in these films. The P–F charge injection is a thermally activated and electric field-assisted thermal hopping mechanism of the charge carriers through the trap levels in the conduction band of the oxide. The current density due to the P–F charge injection is expressed as:

$$J_{P-F} = CE \exp \left( -\frac{q \epsilon_t}{kT} \right)$$

where $$\epsilon_t$$ is the trap ionization energy, as derived from the Arrhenius behavior, and $$\epsilon_t$$ is the dynamic dielectric constant of the film.

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the effective mass of electrons in the oxide. With a reported electron

Figure 6. (Color online) Poole–Frenkel plots measured at different temperatures for the annealed Al2O3 films deposited by (a) thermal ALD and (b) plasma-assisted ALD.

\[ J_{\text{F-N}} = \frac{e^2}{16\pi^2\hbar^2m_{\text{eff}}} E^2 \exp\left(-\frac{4}{3}\frac{m_{\text{ox}}^2}{m_{\text{eff}}} \Phi_b^{3/2}\right) \]  

where \( \Phi_b \) is the barrier height for the tunneling and \( m_{\text{eff}} \) is the effective mass of electrons in the oxide. With a reported electron

effective mass of 0.23\( m_0 \) for \( \text{Al}_2\text{O}_3 \) (Ref. 10), the estimated Al–Al2O3 barrier height values are plotted as a function of the oxide thickness in Fig. 8 for the thermal ALD and plasma-assisted ALD films. The barrier heights generally do not depend on the thickness of the films, which means that any influence of direct tunneling is unlikely, even in the thinnest (5 nm) films investigated here. Annealing does not seem to have a significant influence on the barrier height of the films. However, a clear difference in the barrier height is observed between the thermal and plasma-assisted ALD films. The average Al–Al2O3 barrier height of the latter films is 2.47 ± 0.06 eV, while that of the thermal ALD films is 1.32 ± 0.16 eV. The theoretical Al/Al2O3 barrier height reported by Miyazaki is 2.25 eV, and the photoemission studies by Goodman indicate an Al/Al2O3 barrier height of 2.0 eV. The leakage current through the device, as evident from Eq. 4, increases exponentially with the reducing barrier height and thus a lower barrier height contributes to the larger power consumption of the device.

The \( I-V \) characteristics of the thermal ALD films point to a rather leaky oxide. The leakage current improves considerably after FGA. Plasma-assisted ALD films exhibit a much lower leakage current, which does not change noticeably after FGA. Thermally grown ALD films have a higher thermal activation energy compared to the plasma-assisted ALD films. This is consistent with the \( C-V \) measurements that suggest that the thermal ALD films have more trap states than the plasma-assisted ALD films. Conversely, plasma-assisted ALD has less interface-trap-levels as well, which suggests the impact of the O2 plasma on the nucleation behavior of the film in the early stages of the growth. The chemisorption of the Al-precursor—Al(CH3)3—in the thermal and plasma-assisted ALDs are the same, but after the reaction, the –CH3 ligands are removed in the plasma-assisted ALD by a combustionlike process with the oxygen radicals rather than through a ligand exchange reaction.30-32 Apparently, the oxygen radicals generated in the remote plasma are not only very effective in removing the –CH3 groups and creating a reactive, hydroxylated surface but also create a slightly more dense

Figure 7. (Color online) Fowler–Nordheim tunneling through the annealed Al2O3 films deposited by thermal ALD and plasma-assisted ALD.

\[
\Phi_B = 2.3\times10^{-10} E^{1/2} \left( \frac{E}{V/cm} \right)^{1/2} \quad \text{in} \quad \text{V/cm}^{1/2}
\]

Figure 8. (Color online) Al–Al2O3 barrier heights estimated for the thermal ALD and plasma-assisted ALD Al2O3 films as a function of film thickness in their as-deposited (represented by 5, 10, and 20) and annealed states (represented by 5, 10, and 20 A). The open symbols represent the barrier heights of the as-deposited and the closed symbols represent the barrier heights of the annealed devices.
to large electrical effects, the remaining carbon concentration (e.g., due to unreacted methyl groups) is considered to have a small impact on the electrical properties. This is due to the modest temperature budget during the forming gas anneal which is not able to remove the methyl groups from the films. On the contrary, the amount of hydrogen in the Al₂O₃ film could be an indication for the passivation level. Especially, the difference between the thermal and the plasma ALD processes could be explained by the ability to passivate the dangling bonds with atomic hydrogen during the FGA. Also the density of the film which is slightly higher for the plasma-assisted ALD films is an indication that already during the film growth the atoms are more closely packed, forming an amorphous and denser Al–O–Al network. The discontinuities at the Si interface (not all Si atoms are connected via an oxygen atom to aluminum) and larger density of unreacted –OH groups within a thermally grown film on Si could act as active centers for the electron trapping, thus prompting the thermal ALD films to exhibit Poole–Frenkel charge injection at lower electric fields.

Conclusions

The C–V behaviors of the as-deposited and annealed thin films of Al₂O₃ deposited by the thermal and plasma-assisted ALDs indicate that the plasma technique yields a better Al₂O₃–Si interface from an electrical perspective, though the interfacial oxide thicknesses in both cases are comparable. This is revealed by the flatband voltage shifts of the plasma-assisted ALD films which exhibit a linear relation with the thickness of the oxide. Presumably due to the dominance of mobile ions in the oxide, the thermal ALD films do not exhibit such a linear increase of the flatband voltage shift and, in addition, these films exhibit a large hysteresis in the C–V behavior. The dielectric permittivity of the annealed plasma-assisted Al₂O₃ is relatively high (κ = 8.8) and comparable to bulk Al₂O₃, whereas thermal ALD gives a lower κ-value (κ = 6.7). In addition, the Al–Al₂O₃ barrier height of the plasma-assisted ALD oxides is almost twice larger than that of the thermal ALD oxide, which together with the low defect density explains the origin of the lower leakage currents through the plasma-assisted Al₂O₃ films. The dielectric breakdown electric field of the plasma-assisted ALD Al₂O₃ is 9 MV/cm, whereas the thermal ALD Al₂O₃ breaks down at 5 MV/cm, again confirming the superior quality of the plasma-assisted ALD Al₂O₃ over the thermal Al₂O₃.

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